



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION # 16790GGGeneric Copy

Issue Date: 22-Oct-2014

TITLE: Final PCN for wafer fabrication site addition of ON Semiconductor Niigata Co., Ltd. in Niigata, Japan (Group GG).

PROPOSED FIRST SHIP DATE: starting on 22-Jan-2015 (the actual ship date will be different by each product, please check the responsible Sales person).

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Yasuhiro.Igarashi@onsemi.com.

SAMPLES: Contact your local ON Semiconductor Sales Office or Shigehito.Matsumoto@onsemi.com

ADDITIONAL RELIABILITY DATA: May be available

Contact your local ON Semiconductor Sales Office or Kazutoshi.Kitazume@onsemi.com

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact quality@onsemi.com

DESCRIPTION AND PURPOSE:

This is a Final Process Change Notification to announce the addition of a new wafer fabrication site for the devices covered in this notice. Devices formerly manufactured at the AMPI foundry site will also be manufactured at ON Semiconductor Niigata Co., Ltd. (OSNC) following the expiration of this notice. OSNC located in Niigata, Japan has obtained ISO9001 certification.

The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed for each product to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.

**FINAL PRODUCT/PROCESS CHANGE NOTIFICATION # 16790GG****RELIABILITY DATA SUMMARY****Group GG**

Test:	Conditions:	Interval:	Results
Steady State Operating Life	Tj=150degC	1000 hrs	Pass
High Temperature Reverse Bias	Ta=150degC, VDSS =max	1000 hrs	Pass
Temp Humidity Storage	Ta=85degC, RH=85%	1000 hrs	Pass
Temperature Cycle	Ta=-55degC to 150degC 30min each	100 cycles	Pass
Pressure Cooker	Ta=121degC, 2.03x10 ⁵ Pa, 100%	50 hrs	Pass
High Temperature Storage	Ta=150degC	1000 hrs	Pass
Low Temperature Storage	Ta=-55degC	1000 hrs	Pass
Resistance to Soldering heat(Reflow)	Solder Temp.:260degC±5degC	10s	Pass
Solderability	Solder Temp.: 245degC±5degC	5 s	Pass

ELECTRICAL CHARACTERISTIC SUMMARY

There is no change in the electrical performance. Datasheet specifications remain unchanged.

CHANGED PART IDENTIFICATION

No change to current part marking will occur. Marking traceability codes will be able to identify wafer fab die source.

List of affected General parts:**Group GG**

PART_ID
SCH1333-TL-H